/ Descriptions

Silicon NPN transistor in a TO-92LM Plastic Package.

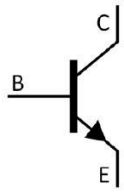
/ Features

Low saturation voltage, high speed switching time, complementary to 2SA1020.

/ Applications

Power amplifier and switching applications.

/ Equivalent Circuit



/ Pinning

PIN1 Base PIN 2 Collector PIN 3 Emitter

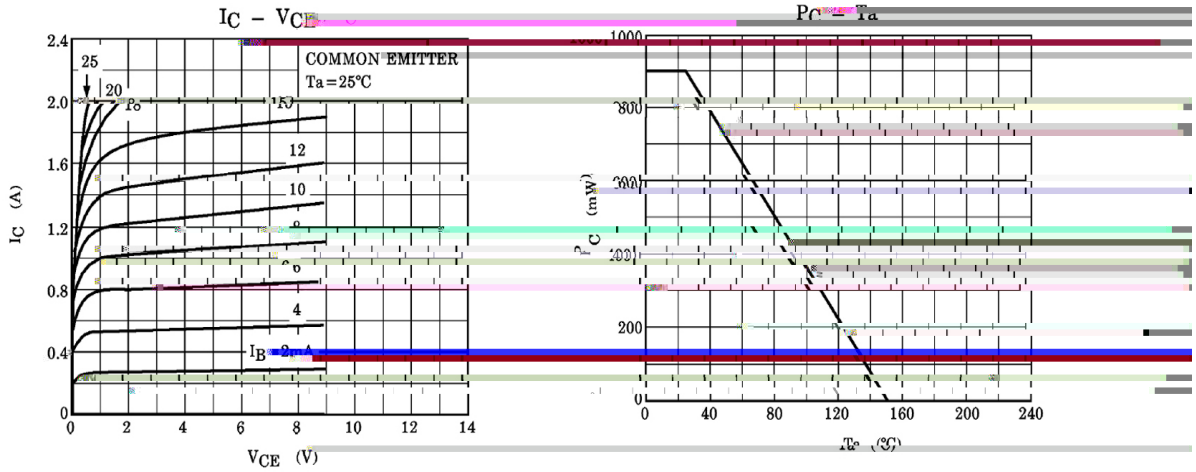
/ h_{FE} Classifications & Marking

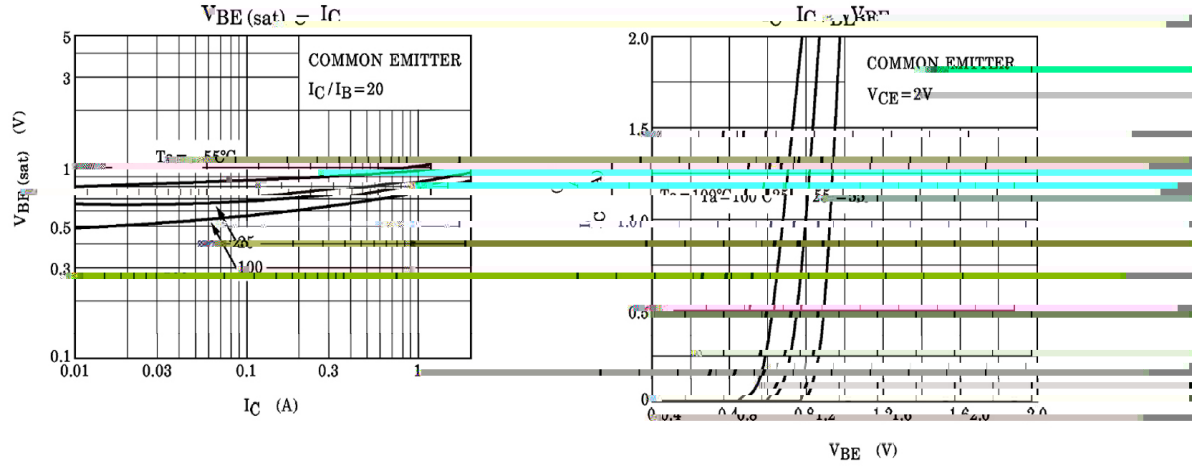
h_{FE} Classifications Symbol	O	Y	G
h_{FE} Range	70 140	120 240	200-400

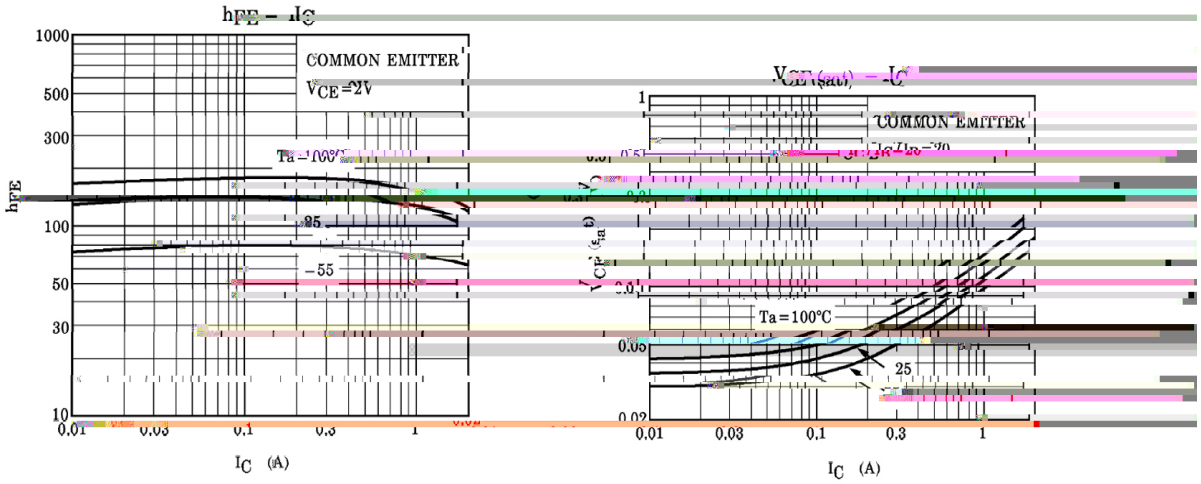
Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	50	V
Collector to Emitter Voltage	V_{CEO}	50	V
Emitter to Base Voltage	V_{EBO}	5.0	V
Collector Current (DC)	I_C	2.0	A
Collector Power Dissipation	P_C	900	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Emitter Breakdown Voltage	V_{CEO}	I_C=10mA I_B=0	50			V
Collector Cut-Off Current	I_{CBO}	V_{CB}=50V I_E=0			1.0	μA
Emitter Cut-Off Current	I_{EBO}	V_{EB}=5.0V I_C=0			1.0	μA
DC Current Gain	$h_{FE(1)}$	V_{CE}=2.0V I_C=0.5A	70		400	
	$h_{FE(2)}$	V_{CE}=2.0V I_C=1.5A	40			
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	I_C=1.0A I_B=0.05A			0.5	V

/ Electrical Characteristic Curve

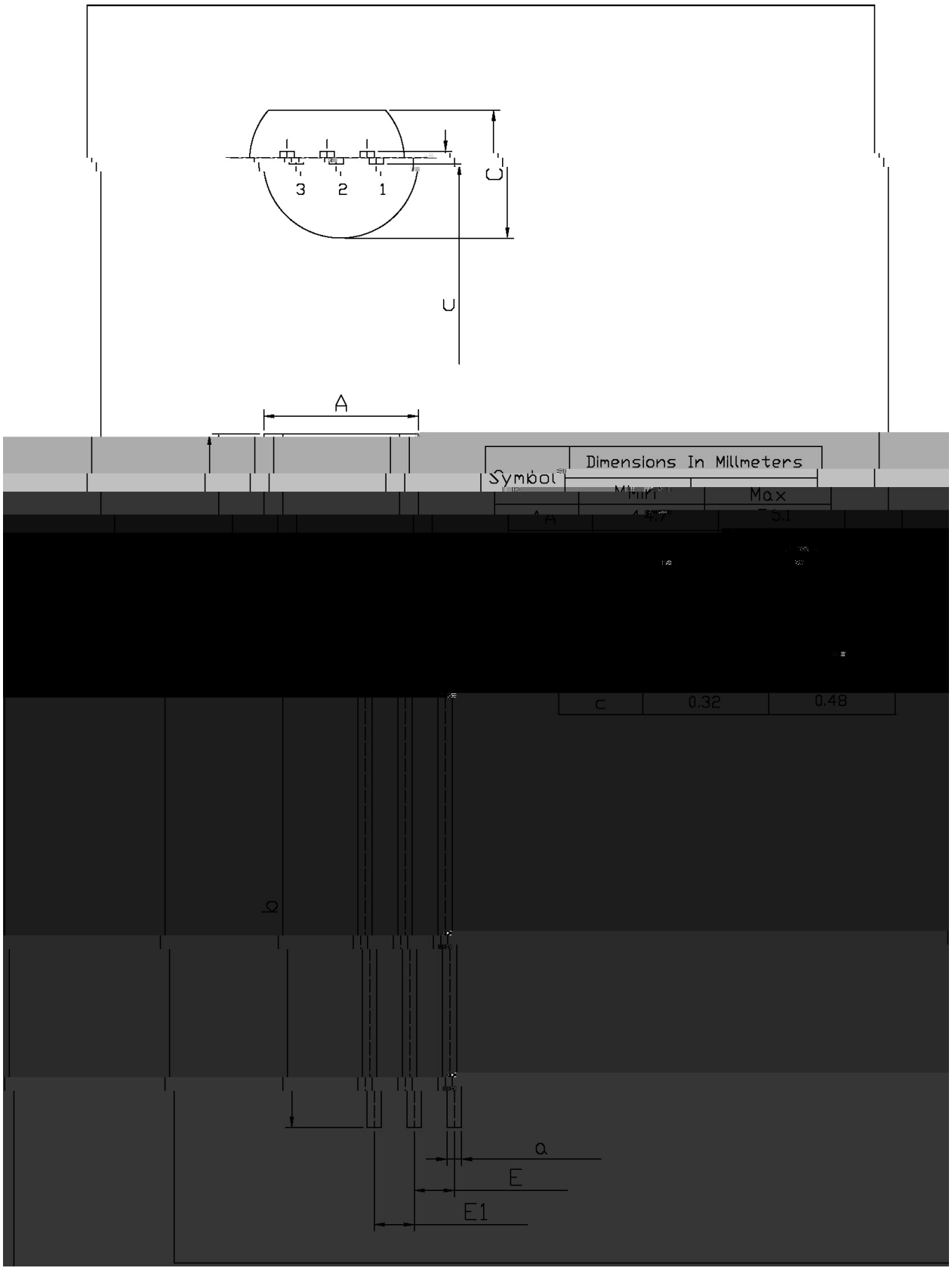




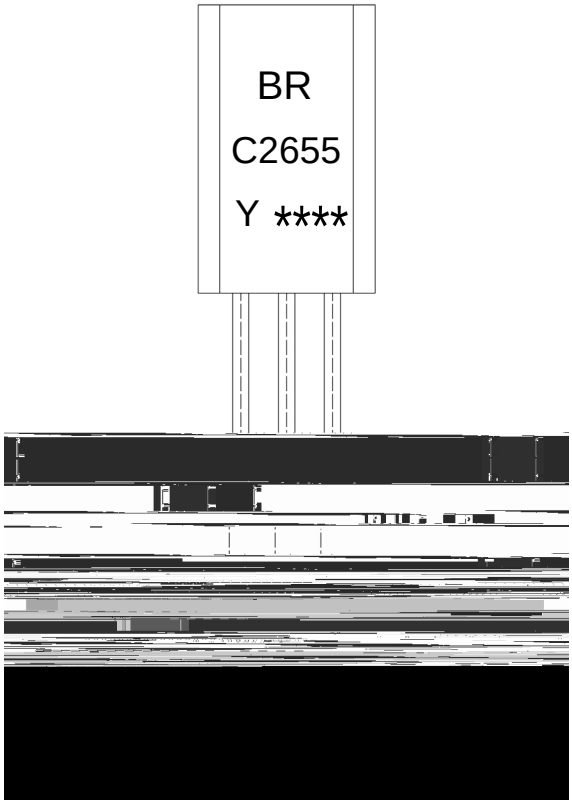


/ Package Dimensions

TO-92LM Unit: mm



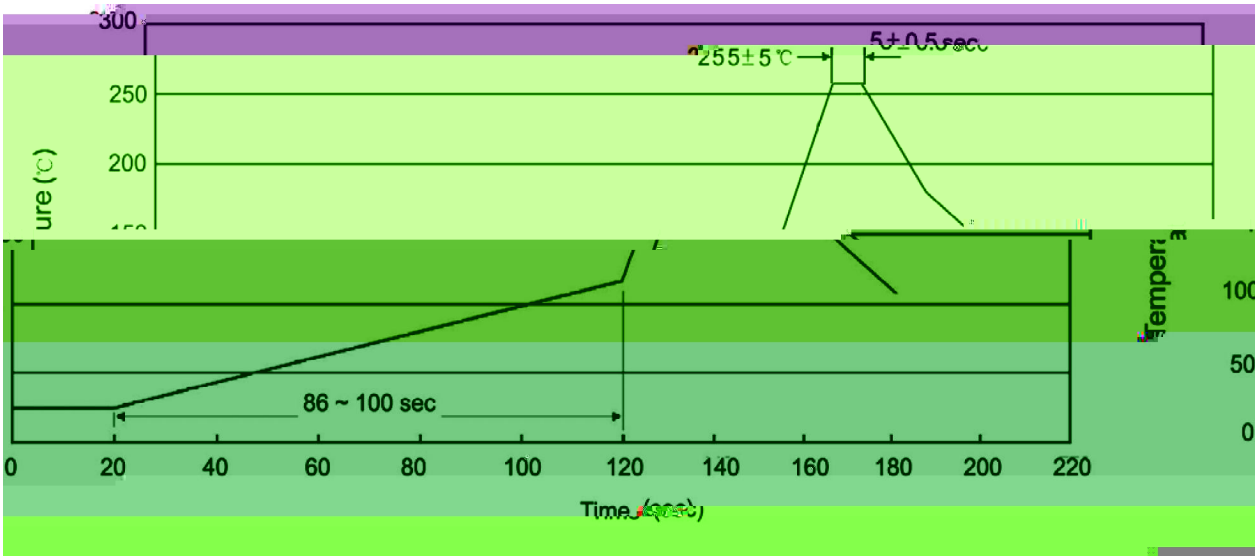
/ Marking Instructions



Note:

BR:	Company Code.
C2655:	Product Type.
Y:	h_{FE} Classifications Symbol
****:	Lot No. Code,code change with Lot No.

( ) / Temperature Profile for Dip Soldering(Pb-Free)



	Note:
1 25 150 60 90sec;	1.Preheating:25~150 , Time:60~90sec.
2 255 5 5 0.5sec;	2.Peak Temp.:255 5 , Duration:5 0.5sec.
3 2 10 /sec.	3. Cooling Speed: 2~10 /sec.

/ Resistance to Soldering Heat Test Conditions

270 5	10 1 sec.	Temp.:270±5	Time:10±1 sec

/ Packaging SPEC.

/ BULK

Package Type	Units	Dimension	(unit mm3)